FM3808

256Kb Bytewide FRAM w/Real-Time Clock



Features

256K bit Ferroelectric NonVolatile RAM

- Organized as 32,752 x 8 bits
- High Endurance 100 Billion (10¹¹) Read/Writes
- 10 year Data Retention
- NoDelayTM Writes
- 70 ns Access Time/ 130 ns Cycle Time
- Built-in Low V_{DD} Protection

Real-Time Clock/Calendar Function

- Clock Registers in Top 16 bytes of Address Space
- Backup Power from External Capacitor or Battery
- Tracks Seconds through Centuries in BCD Format
- Tracks Leap Years through 2099
- Runs from a 32.768 kHz Timekeeping Crystal

System Supervisor Function

- Programmable Clock/Calendar Alarm
- Programmable Watchdog Timer
- Programmable Power Supply Monitor
- Interrupt Output Programmable active high/low
- Control Settings Inherently NonVolatile
- Generates either Processor Reset or Interrupt

Low Power Operation

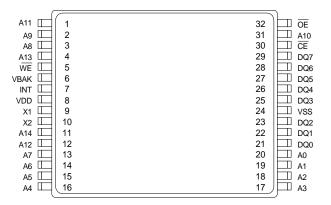
- 5V Operation for Memory and Clock Interface
- Backup Voltage as low as 2.5V
- 25 mA I_{DD} Active Current
- 1 μA I_{BAK} Clock Backup Current

Description

The FM3808 combines a 256Kb FRAM array with a real-time clock and a system supervisor function. The timekeeping function is driven by a user supplied 32.768 kHz crystal. It maintains time and date settings in the absence of system power through the user's choice of backup power source - either capacitor or battery. In either case data in the memory array does not depend on the backup source, it remains nonvolatile in FRAM. In addition to timekeeping, the FM3808 includes a system supervisor to manage low V_{DD} power conditions and a watchdog timer function. A programmable interrupt output pin allows the user to select the supervisor functions and the polarity of the signal.

Both the FRAM array and the timekeeping function are accessed through the memory interface. The upper 16-address locations of the memory space are allocated to the timekeeping registers rather than to memory. The FRAM array provides data retention for 10 years in the absence of system power, and is not dependent on the backup power source used for the clock. This eliminates system concerns over data loss in a traditional battery-backed RAM solution. In addition, clock and supervisor control settings are implemented in FRAM rather than battery-backed RAM, making them more dependable. The FM3808 offers guaranteed operation over an industrial temperature range of -40°C to +85°C.

Pin Configuration



Ordering Information						
FM3808-70-T	70 ns access, 32-pin TSOP					
FM3808DK	DIP module development kit					

Documentation for the DIP module development kit is provided separately.

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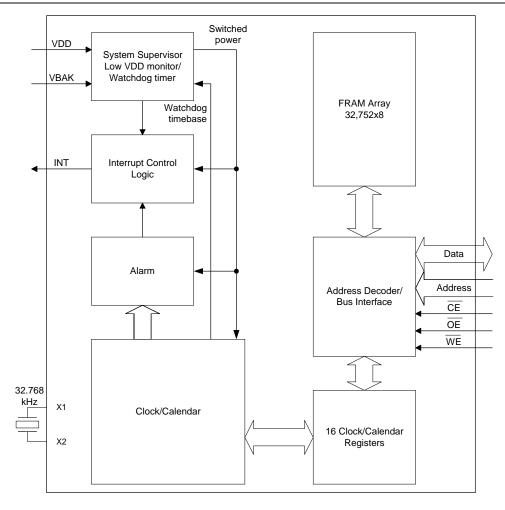


Figure 1. Block Diagram

Pin Description

Pin Name	I/O	Pin Description
A0-A14	Input	Address: The 15 address inputs select one of 32,752 bytes in the FRAM array or one of
		16 bytes in the clock/calendar. The address is latched on the falling edge of /CE.
DQ(7:0)	I/O	Data: Bi-directional 8-bit data bus for accessing the FRAM array and clock.
/CE	Input	Chip Enable: The active low /CE input selects the device. The falling edge of /CE
		internally latches the address. Address changes that occur after /CE has transitioned
		low are ignored until the next falling edge occurs.
/OE	Input	Output Enable: The active low /OE input enables the data output buffers during read
		cycles. Deasserting /OE high causes the DQ pins to tri-state.
/WE	Input	Write Enable: The active low /WE low enables data on the DQ pins to be written to the
		address location latched by the falling edge of /CE.
X1, X2	Input	Connect 32.768 kHz crystal.
INT	Output	Interrupt output: This output can be programmed to respond to the clock alarm, the
		watchdog timer, and the power monitor. It is programmable to either active high
		(push/pull) or active low (open-drain).
V_{BAK}	Supply	Backup Supply Voltage: This supply is used to maintain power for the clock. It must
		remain between 2.5V and V_{DD} -0.3V. Typically it is supplied by either a capacitor or a
		battery. Current is drawn from V_{BAK} when V_{DD} is below the V_{BAK} voltage.
V_{DD}	Supply	Supply Voltage: 5V
V_{SS}	Supply	Ground.



Functional Truth Table

/CE	/WE	/OE	Function
Н	X	X	Standby/Precharge
И	X	X	Latch Address
L	Н	L	Read
L	L	X	Write

Overview

The FM3808 integrates three complementary but distinct functions under a common interface in a single package. First, is the 32Kx8 FRAM memory block (minus 16 bytes), second is the real-time clock/calendar, and third is the system supervisor. The functions are integrated to enhance their individual performance, so that each provides better capability than three similar stand-alone devices. All functions use the same bytewide address/data interface and are memory mapped. Special functions including the clock and supervisor are controlled by registers that reside in the top of the combined

memory map. The register map is described below, followed by a detailed description of each functional block.

Register Map

The interface to clock and supervisor functions is via 16 address locations at the top of the address space. The registers contain timekeeping data, control bits, or information flags. A short description of each register follows. Detailed descriptions of each function follow the register summary.

Register Map Summary Table

				Da	ata					
Address	D7	D6	D5	D4	D3	D2	D1	D0	Function	Range
7FFFh		10 y	ears			ye	ars		Years	00-99
7FFEh	0	0	0	10 mo		moi	nths		Month	1-12
7FFDh	0	0	10 (date		da	ate		Date	1-31
7FFCh	0	0	0	0	0 day				Day	1-7
7FFBh	0	0	10 h	ours		ho	urs		Hours	0-23
7FFAh	0		10 minutes			min	utes		Minutes	0-59
7FF9h	0		10 seconds	}		seco	onds		Seconds	0-59
7FF8h	/OSCEN	reserved	reserved	CALS	CAL3	CAL2	CAL1	CAL0	Control-NV	
7FF7h	WDS	/WDW	WDT5	WDT4	WDT3	WDT2	WDT1	WDT0	Watchdog	
7FF6h	WIE	AIE	PFE	ABE	H/L	P/L	VINT	reserved	Interrupts	
7FF5h	/Match	0	Alarm	10 date		Alarn	n date	=	Alarm Date	1-31
7FF4h	/Match	0	Alarm 1	0 hours		ho	urs		Alarm Hours	0-23
7FF3h	/Match	Ala	rm 10 minu	tes		Alarm ı	minutes		Alarm Minutes	0-59
7FF2h	/Match	Ala	rm 10 seco	nds	Alarm seconds				Alarm Seconds	0-59
7FF1h									User-NV	
7FF0h	WDF	AF	PF	CF	TST	CAL	W	R	Flags/Control	

Note that the shaded bits are implemented in FRAM and therefore are nonvolatile even without backup power.



Table 1. Register Map

Address Description

7FFFh	Timekeep	Timekeeping – Years										
	D7	D6	D5	D4	D3	D2	D1	D0				
	10 year.3	10 year.2	10 year.1	10 year.0	Year.3	Year.2	Year.1	Year.0				
	Contains th	Contains the lower two BCD digits of the year. Lower nibble contains the value for years; upper nibble										
	contains the	e value for 10	s of years. Ea	ch nibble op	erates from 0	to 9. The ran	ge for the reg	gister is 0-99.				

7FFEh	Timekeeping – Months										
	D7	D6	D5	D4	D3	D2	D1	D 0			
	0	0	0	10 Month	Month.3	Month.2	Month.1	Month.0			
		C		h. Lower nibl per digit and		U		s from 0 to 9; register is 1-			

7FFDh	Timekeep	Timekeeping – Date of the month										
	D7	D7 D6 D5 D4 D3 D2 D1 D0										
	0	0	10 date.1	10 date.0	Date.3	Date.2	Date.1	Date.0				
	Contains the BCD digits for the date of the month. Lower nibble contains the lower digit and open											
	from 0 to 9; upper nibble contains the upper digit and operates from 0 to 3. The range for the register											
	1-31.											

7FFCh	Timekeep	ing – Day o	of the week									
	D7	D6	D5	D4	D3	D2	D1	D0				
	0	0	0	0	0	Day.2	Day.1	Day.0				
	Lower nibb	Lower nibble contains a value that correlates to day of the week. Day of the week is a ring counter that counts from 1 to 7 then returns to 1. The user must assign meaning to the day value, as the day is not										
	counts from											
	integrated v	with the date.										

7FFBh	Timekeep	Timekeeping – Hours										
	D7	D7 D6 D5 D4 D3 D2 D1 D0										
	0	0	10 hours.1	10 hours.0	Hours.3	Hours2	Hours.1	Hours.0				
		upper nibble					U	t and operates range for the				

7FFAh	Timekeep	ing – Minu	tes								
	D7	D6	D5	D4	D3	D2	D1	D0			
	0	10 min.2	10 min.1	10 min.0	Min.3	Min.2	Min.1	Min.0			
	Contains th	Contains the BCD value of minutes. Lower nibble contains the lower digit and operates from 0 to 9;									
	upper nibbl	le contains the	e upper minu	tes digit and o	operates from	0 to 5. The r	ange for the i	register is 0-59.			

7FF9h	Timekeep	ing – Secon	ıds							
	D7	D6	D5	D4	D3	D2	D1	D 0		
	0	10 sec.2	10 sec.1	10 sec.0	Seconds.3	Seconds.2	Seconds.1	Seconds.0		
	Contains the BCD value of seconds. Lower nibble contains the lower digit and operates from 0 to 9; upper nibble contains the upper digit and operates from 0 to 5. The range for the register is 0-59.									
	upper nibbl	e contains the	e upper digit a	and operates	from 0 to 5.	The range for	the register is	s 0-59.		



Address Description

7FF8h	Control-Nonvolatile										
	D7	D6	D5	D4	D3	D2	D1	D0			
	OSCEN	Reserved	Reserved	CALS	CAL.3	CAL.2	CAL.1	CAL.0			
/OSCEN	/Oscillator Enable. When set to 1, the oscillator is halted. When set to 0, the oscillator runs. Disabling										
	the oscillate	or can save ba	attery power o	during storage	e. On a no ba	ttery power u	p, this bit is s	set to 1.			
Reserved	Do not use.	Should rema	in set to 0.								
CALS	Calibration	sign. Determ	ines if the ca	libration adju	stment is app	lied as an add	dition to or as	s a subtraction			
	from the time-base. This bit is implemented in FRAM. Calibration is explained below										
CAL.3-0	These four	bits control th	ne calibration	of the clock.	These bits an	e implemente	ed in FRAM.				

7FF7h	Watchdog	g Timer												
	D7	D6	D5	D4	D3	D2	D1	D0						
	WDS	WDW	WDT.5	WDT.4	WDT.3	WDT.2	WDT.1	WDT.0						
WDS	WDS Watchdog Strobe. Setting this bit to 1 reloads and restarts the watchdog timer. Setting the bit to 0 haffect. The bit is cleared automatically once the watchdog timer is reset. The WDS bit is write only							bit to 0 has no						
								rite only.						
	Reading it always will return a 0.													
/WDW	Watchdog Write Enable. Setting this bit to 1 masks the watchdog timeout value (WDT.5-0) so it cannot													
	be written. This allows the user to strobe the watchdog without disturbing the timeout value. Setting this													
						0 0		ew value will be						
			_		•	is complete.	This function	is explained						
			chdog Timer											
WDT.5-0								this register.						
	It represents a multiplier of the 32 Hz count (31.25 ms). The minimum range or timeout value is 31.25													
	ms (a setting of 1) and the maximum timeout is 2 seconds (setting of 3Fh). Setting the watchdog timer													
	register to 0 disables the timer. These bits can be written only if the /WDW bit was cleared to 0 on a													
	previous cy	cle.						previous cycle.						

7FF6h	Interrupts	S							
	D7	D6	D5	D4	D3	D2	D1	D0	
	WIE	AIE	PFE	ABE	H/L	P/L	VINT	Reserved	
WIE	Watchdog Interrupt Enable. When set to 1 and a watchdog timeout occurs, the watchdog timer drive							imer drives	
		the interrupt pin as well as the WDF flag. When set to 0, the watchdog timeout affects only the WDF							
AIE	Alarm Inter	rupt Enable.	When set to	1, the alarm n	natch drives t	he interrupt p	in as well as	the AF flag.	
	When set to	0, the alarm	match only a	affects the AF	flag.			_	
PFE	Power-fail I	nterrupt Ena	ble. When se	t to 1, the pov	ver-fail moni	tor drives the	pin as well a	s the PF flag.	
	When set to	0, the power	r-fail monitor	affects only	the PF flag.				
ABE	Alarm Batte	ery-backup E	nable. When	set to 1, the a	larm interrup	t (as controll	ed by AIE) w	rill function	
	even in batt	ery backup n	node. When s	et to 0, the al	arm will occu	r only when	VDD>VLO.		
H/L	High/Low.	When set to	a 1, the Interr	upt pin is pus	h/pull active	high. When s	set to a 0, the	interrupt pin	
		n active low.							
P/L				rrupt pin is dı					
				en set to a 0,	the interrupt	pin is driven	to an active l	evel (as set by	
		he flag regist							
VINT			C				C	o a 1, the flag	
				ng occurs at 4	.6V. The inte	rrupt pin is ei	nabled by the	PFE bit,	
	otherwise of	nly an intern	al flag is set.						

7FF5h	Alarm – Date of the month								
	D7	D7 D6 D5 D4 D3 D2 D1 D0							
	M	0	10 date.1	10 date.0	Date.3	Date.2	Date.1	Date.0	
	Contains th	Contains the alarm value for the date of the month and the mask bit to select or deselect the date value.							
/M	Match. Sett	Match. Setting this bit to 0 causes the date value to be used in the alarm match. Setting this bit to 1							
	causes the match circuit to ignore the date value.								



Description

7FF4h	Alarm – H	Alarm – Hours							
	D7	D7 D6 D5 D4 D3 D2 D1 D0							
	M	0	10 hours.1	10 hours.0	Hours.3	Hours2	Hours.1	Hours.0	
	Contains the	Contains the alarm value for the hours and the mask bit to select or deselect the hours value.							
/M	Match. Sett	Match. Setting this bit to 0 causes the hours value to be used in the alarm match. Setting this bit to 1							
	causes the r	natch circuit	to ignore the	hours value.					

7FF3h	Alarm – N	Alarm – Minutes								
	D7	D7 D6 D5 D4 D3 D2 D1 D0								
	M	10 min.2	10 min.1	10 min.0	Min.3	Min.2	Min.1	Min.0		
	Contains th	Contains the alarm value for the minutes and the mask bit to select or deselect the minutes value								
/M	Match. Sett	Match. Setting this bit to 0 causes the minutes value to be used in the alarm match. Setting this bit to 1								
	causes the r	natch circuit	to ignore the	minutes valu	e.					

7FF2h	Alarm – S	Alarm – Seconds							
	D7	D7 D6 D5 D4 D3 D2 D1 D0							
	M	10 sec.2	10 sec.1	10 sec.0	Seconds.3	Seconds.2	Seconds.1	Seconds.0	
	Contains th	Contains the alarm value for the seconds and the mask bit to select or deselect the minutes value.							
/M	Match. Sett	Match. Setting this bit to 0 causes the seconds value to be used in the alarm match. Setting this bit to 1							
	causes the i	match circuit	to ignore the	seconds valu	e.				

7FF1h	User-NonVolatile								
	D7 D6 D5 D4 D3 D2 D1 D0								
	This register is an uncommitted nonvolatile register. The user register is not manipulated by the real-time clock other than to provide nonvolatile storage of the contents.								

7FF0h	Flags/Control							
	D7	D6	D5	D4	D3	D2	D1	D0
	WDF	AF	PF	CF	TST	CAL	W	R
WDF						ner is allowed . It is read-on		without being er.
AF	Alarm Flag	Alarm Flag. This bit is set to 1 when the time and date match the values stored in the alarm registers with the match $bit(s) = 0$. It is cleared when the Flag register is read. It is read-only for the user.						
PF		Power-fail Flag. This bit is set to 1 when power falls below the power-fail interrupt threshold VINT. It is cleared to 0 when the Flag register is read. It is read-only for the user.						
CF	Century Overflow Flag. This bit is set to a 1 when the values in the years register overflows from 99 to 00. This indicates a new century, such as going from 1999 to 2000 or 2099 to 2100. The user should record the new century information as needed. This bit is cleared to 0 when the Flag register is read. It is read-only for the user.							
TST	Invokes fac	tory test mod	e. Users shou	ıld always set	this bit to 0.			
CAL	Calibration operates no:		set to 1, the	clock enters	calibration m	ode. When C	AL is set to 0), the clock
W	Write Time. Setting the W bit to 1 freezes updates of the timekeeping registers. The user can then write them with updated values. Setting the W bit to 0 causes the contents of the time registers to be transferred to the timekeeping counters. This bit affects registers xF, xF, xD, xC, xB, xA, and x9							
R	transferred to the timekeeping counters. This bit affects registers xF, xE, xD, xC, xB, xA, and x9. Read Time. Setting the R bit to 1 copies a static image of the timekeeping registers and places them in a holding register. The user can then read them without concerns over changing values causing system errors. The R bit going from 0 to 1 causes the timekeeping capture, so the bit must be returned to 0 prior to reading again. This bit affects registers xF, xE, xD, xC, xB, xA, and x9.							



Real-time Clock Operation

The real-time clock (RTC) consists of an oscillator, a divider, and a register system to access the information. It divides down the 32.768 kHz time-base to provide the user timekeeping resolution of one second (1Hz). Static registers provide the user with read/write access to the time values. The synchronization of these registers with the timekeeper core is performed using R and W bits in register 7FF0h.

Setting the R bit from 0 to 1 causes a transfer of the timekeeping information to holding registers that can be read by the user. If a timekeeper update is in progress when the R is set, the update will be completed prior to loading the registers. Another update cannot be performed unless the R bit is first cleared to 0 again.

Setting the W bit causes the timekeeper to freeze updates. Clearing it to 0 causes the values in the time registers to be written into the timekeeper core. Users should be sure not to load invalid values, such as FFh to any of the timekeeping registers.

Updates to the timekeeping core occur continuously except when frozen. A diagram of the timekeeping core is shown below.

Backup Power

The real-time clock/calendar is intended for permanently powered operation. When primary system power fails, the voltage on V_{DD} will drop. When it crosses the voltage on the V_{BAK} supply pin, the clock power will switch to the backup power supply V_{BAK} . The supervisor function, described below, controls the switchover process as part of a more complete power management circuit.

The clock uses very little current which maximizes battery life. Although a backup battery may be used with the FM3808, the key advantage to combining a clock function with FRAM is that the configuration data (shaded regsiter bits in Table 2) is nonvolatile and does not require a battery backup power source. Therefore, it is more practical to use a capacitor as a backup energy source than a battery-backed RAM/clock combo. With the FM3808, the user has the choice of using a battery or a capacitor as the backup source. Some of the parameters used in the capacitor vs. battery decision include the expected duration of power outages, the difficulty of resetting the time if lost, and the cost tradeoff of using a small battery versus a capacitor.

The following functions are powered from the backup power source when $V_{DD} < V_{BAK}$ (backup mode):

- Clock/calendar core
- Alarm interrupt/comparator
- INT pin driver (determined by ABE & AIE bits); active low only
- Flags connected to related functions

The following functions are not powered and are disabled when $V_{\text{DD}} \! < V_{\text{LO}}$:

- User interface
- Watchdog timer
- Power monitor & band-gap $(V_{DD} < \approx 2.0V)$
- Flags connected to related functions
- All FRAM access & updates
- Calibration operation
- INT driver if active high is programmed



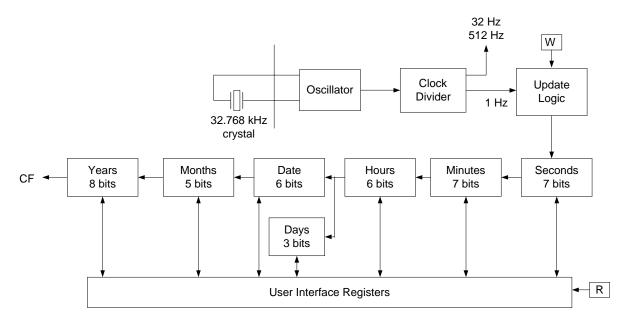


Figure 2. Real-time Clock Core Block Diagram

Calibration

When the CAL bit in register 7FF0.2 is set to 1, the clock enters calibration mode. Interrupts are disabled in CAL mode. Calibration operates by applying a digital correction to the counter based on the frequency error. In CAL mode, the INT pin is driven with a 512 Hz nominal square wave. Any measured deviation from 512 Hz is converted into an error in ppm. This error corresponds to a correction value that must then be written by the user into the calibration register 7FF8h. The correction factors are listed in the Table 2.

Positive ppm errors require a negative adjustment that removes pulses. Negative ppm errors require a positive correction that adds pulses. Positive ppm adjustments have the CALS bit set to 1, where as negative ppm adjustments have CALS = 0. After calibration, the clock will have a maximum error of

 $\pm\,4.34$ ppm or $\pm\,0.19$ minutes per month at the calibrated temperature.

The calibration setting is nonvolatile and is stored in 7FF8.4-0. This value only can be written when the CAL bit is set to a 1. To exit calibration mode, the user should clear the CAL bit to a 0.

When the calibration mode is entered, the user can measure the frequency error on the INT pin. This error expressed in ppm translates directly into timekeeping error. An offsetting calibration adjustment corrects this error. However, the correction is applied by adding or removing pulses on a periodic basis. Therefore, the correction will not appear on the 512 Hz output. The calibration correction must be applied using the values shown in Table 2. The timekeeping accuracy can be verified by comparing the FM3808 time to a reference source.



Table 2. Calibration Adjustments

	Measured Fre	quency Range	Error Rar	nge (ppm)	
	Min	Max	Min	Max	Program Calibration D4-D0
0	512.0000	511.9978	0	4.34	00000b
1	511.9978	511.9933	4.35	13.02	10001b
2	511.9933	511.9889	13.03	21.70	10010b
3	511.9889	511.9844	21.71	30.38	10011b
4	511.9844	511.9800	30.39	39.06	10100b
5	511.9800	511.9756	39.07	47.74	10101b
6	511.9756	511.9711	47.75	56.42	10110b
7	511.9711	511.9667	56.43	65.10	10111b
8	511.9667	511.9622	65.11	73.78	11000b
9	511.9622	511.9578	73.79	82.46	11001b
10	511.9578	511.9533	82.47	91.14	11010b
11	511.9533	511.9489	91.15	99.82	11011b
12	511.9489	511.9444	99.83	108.50	11100b
13	511.9444	511.9400	108.51	117.18	11101b
14	511.9400	511.9356	117.19	125.86	11110b
15	511.9356	511.9311	125.87	134.54	11111b
	Measured Fre	quency Range	Error Rar	nge (ppm)	
	Min	Max	Min	Max	Program Calibration D4-D0
0	512.0000	512.0022	0	4.34	00000b
1	512.0022	512.0067	4.35	13.02	00001b
2	512.0067	512.0111	13.03	21.70	00010b
3	512.0111	512.0156	21.71	30.38	00011b
4	512.0156	512.0200	30.39	39.06	00100b
5	512.0200	512.0244	39.07	47.74	00101b
6	512.0244	512.0289	47.75	56.42	00110b
7	512.0289	512.0333	56.43	65.10	00111b
8	512.0333	512.0378	65.11	73.78	01000b
9	512.0378	512.0422	73.79	82.46	01001b
10	512.0422	512.0467	82.47	91.14	01010b
11	512.0467	512.0511	91.15	99.82	01011b
12	512.0511	512.0556	99.83	108.50	01100b
13	512.0556	512.0600	108.51	117.18	01101b
14	512.0600	512.0644	117.19	125.86	01110b
15	512.0644	512.0689	125.87	134.54	01111b



Supervisor Operation

The Supervisor function includes a clock/calendar alarm, a watchdog timer, and a power monitor. A programmable interrupt pin provides maximum functionality to permit the host processor to benefit from the supervisor functions. It is designed to allow either reset or interrupt capability to the external processor host.

Alarm

The alarm function compares user-programmed values to the corresponding time of day values. When a match occurs, the alarm event occurs. The alarm offers an internal flag bit and an optional external interrupt.

There are four alarm match values. They are date of the month, hours, minutes, and seconds. The match select bits determine if a value is used in the alarm match selection. Setting the match select bit to '0' indicates that the corresponding value should be used in the match process.

Depending on the match select bits, the alarm can occur as specifically as one particular second on one day of the month, or as frequently as once per second

continuously. Each match select bit is contained in the MSB of the match value register. The match select bits work in concert as shown in the table below. Selecting none of the match bits (all '1's) indicates that no match is required. The alarm occurs every second. Setting the match select bit for seconds to '0' causes the logic to match the seconds alarm value to the current time of day. Since a match will occur for only one value per minute, the alarm occurs once per minute. Likewise setting the seconds and minutes match select bits causes an exact match of these values. Thus, an alarm will occur once per hour. Setting seconds, minutes, and hours causes a match once per day. Lastly, selecting all match-values causes an exact time and date match. Selecting other bit combinations will not produce meaningful results, however the alarm circuit should follow the functions described.

The alarm event can be detected by the user in two ways. First, the AF flag bit in the register 7FF0.6 will indicate that a match has occurred. The AF bit will be set to 1 when a valid match occurs. Reading the flag register clears the alarm flag bit (and all others). Second, a hardware interrupt pin will be provided. The interrupt function is described below.

Alarm Match Bits

Seconds	Minutes	Hours	Date	Alarm condition
1	1	1	1	No match required = alarm 1/second
0	1	1	1	Alarm when seconds match, = alarm 1/minute
0	0	1	1	Alarm when seconds, minutes match, = alarm 1/hour
0	0	0	1	Alarm when seconds, minutes, hours match, = alarm 1/day
0	0	0	0	Alarm when seconds, minutes, hours, date match, = alarm 1/month



Watchdog Timer

The Watchdog timer is a free running down counter that uses the 32 Hz clock (31.25 ms) derived from the crystal oscillator. The oscillator must be running (/OSCEN=0) for the watchdog to function. It begins counting down from the value loaded in the Watchdog timer register (7FF7h).

The counter consists of a loadable register and a free running counter. On power up, the watchdog timeout value in 7FF7h is loaded into the counter load register. Counting begins on power up and restarts from the loadable value any time the Watchdog Strobe (WDS – 7FF7.7) WDS bit is set to 1. The counter is compared to terminal value of 0. If the counter reaches this value, it causes an internal flag and an optional interrupt output (see interrupts below). The user can prevent the timeout interrupt by setting WDS bit to 1 prior to the counter reaching 0. This causes the counter to be reloaded with the watchdog timeout value and to be restarted. As long as the user sets the WDS bit prior to the counter

reaching the terminal value, the interrupt and flag never occurs.

New timeout values can be written by setting the watchdog write bit (/WDW – 7FF7.6) to 0. When the /WDW bit is 0 (from a previous operation), new writes to the watchdog timeout value 7FF7.5-0 allow the timeout value to be modified. When /WDW is a 1, then writes to bits 7FF7.4-0 will be ignored. The /WDW function allows a user to set the WDS bit without concern that the watchdog timer value will be modified. A logical diagram of the watchdog timeout value to 0 would be otherwise meaningless and therefore disables the watchdog function.

The output of the watchdog timer is a flag bit (WDF – 7FF0.7) that is set if the watchdog is allowed to timeout. The flag is set upon a watchdog timeout and cleared when the flag register is read by the user. The user can also enable an optional interrupt source to drive the interrupt pin if the watchdog timeout occurs. The interrupt function is described below.

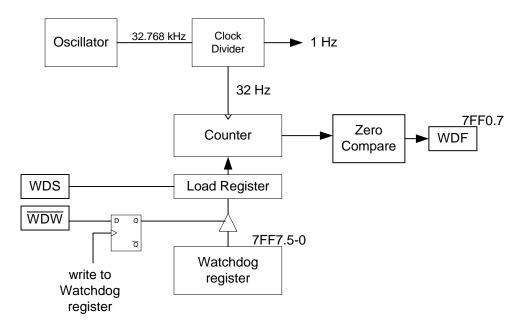


Figure 3. Watchdog Timer Block Diagram



Power Monitor

The FM3808 provides a power management scheme with either power-fail interrupt or processor-reset capability. It also controls the internal switch to backup power for the timekeeper and protects the memory from low- $V_{\rm DD}$ access. The power monitor is based on an internal band-gap reference circuit that compares the incoming $V_{\rm DD}$ to various thresholds.

The power monitor compares V_{DD} to three thresholds. The first is an interrupt threshold (V_{INT}) , which can be selected between two levels as shown below. When V_{DD} drops below the programmed V_{INT} level, the event will set the power fail flag (PF – 7FF0.5). It also can drive the interrupt pin as described in the interrupt section below. The interrupt level selection is controlled via the voltage interrupt bit $(V_{INT}$ – 7FF6.1) as follows.

Power fail	V_{INT}
4.6V	0
4.75V	1

If the power monitor is used to reset the external processor, then the lower threshold is more likely to be used. If the power monitor is providing an early warning interrupt, then either may be suitable depending on expected slew rates and the amount of data to be saved on power failure.

The second threshold is the low V_{DD} memory lockout. This level, which is called V_{LO} , prevents low voltage writes to the FRAM array, which may result in lost data. At this time, access to the memory array and clock registers will be blocked until V_{DD} rises above V_{LO} . V_{LO} is always below V_{INT} . When V_{DD} is below V_{LO} , inputs will be ignored. On power up, the chip enable input will be ignored while V_{DD} is below V_{LO} , but must be inactive (high) when V_{DD} reaches the V_{LO} level.

The third threshold is the switch of the internal supply from V_{DD} to V_{BAK} for the timekeeper. This switchover will occur at the level when V_{DD} crosses

below V_{BAK} . When switchover occurs, the clock will begin to draw power from V_{BAK} rather than V_{DD} . This event may be above or below the V_{INT} or V_{LO} level depending on whether a battery or capacitor backup is used.

To conserve the life of the backup source, the power monitor circuit is only operated from $V_{DD}.$ When V_{DD} has dropped too low for the monitor to work, it ceases operation. However, the power monitor will reenergize as V_{DD} rises on power-up. On power-up, after the band-gap energizes, the reverse sequence will occur. As soon as the band gap is functional, it will re-assert both selections for switch over and power fail. As the V_{DD} rises further, the switchover will be removed, allowing memory access and operating the clock from $V_{DD}.$ As the V_{DD} rises above $V_{INT},$ the power-fail condition will be removed. Note that the PF flag will not be cleared until the flag register is read.

The following figure illustrates the various events tracked by the power monitor.



Figure 4. Power Monitor Events

In the diagram, BG is the voltage at which the bandgap will function. This voltage is not precisely specified but is well below the range of operation for the memory or other circuits. On power down, the band-gap will monitor V_{DD} as long as possible. This allows a brownout to occur where V_{DD} returns to a proper level prior to the band-gap failing. Since the band-gap runs only from V_{DD} , it does not reduce the life of the backup source.



Interrupts

The supervisor was designed to serve diverse applications. Its sophistication is managed by the interrupt block, which makes this functionality available to the host system. The interrupt block is capable of providing interrupt or reset conditions, and even can power up a system at a preprogrammed time. The function is described as an interrupt, even though the output may be used as a reset source.

The supervisor provides three potential interrupt sources. They include the watchdog timer, the power monitor, and the clock/calendar alarm. Each can be individually enabled and assigned to drive the single INT pin. In addition, each has a flag bit associated with it so that the host processor can determine the cause of the interrupt.

Some of the sources have additional control bits that determine functional behavior. In addition, the pin driver has three bits that specify its behavior when an interrupt occurs. A functional diagram of the interrupt logic is shown below.

As shown, the three interrupts each have a source and an enable. Both the source and the enable must be active (true high) in order to generate an interrupt output. Only one source is necessary to drive the pin. The user can identify the source by reading the flag register, which contains the flags associated with each source. All flags are cleared to 0 when the register is read. The cycle must be a complete read cycle, otherwise the flags will not be cleared if the /WE signal goes low. The power monitor has two programmable settings that are explained above in the power monitor section.

Once an interrupt source is active, the pin driver determines the behavior of the output pad. It has two programmable settings as shown below. Pin driver control bits are located in the Interrupts register 7FF6h.3-2.

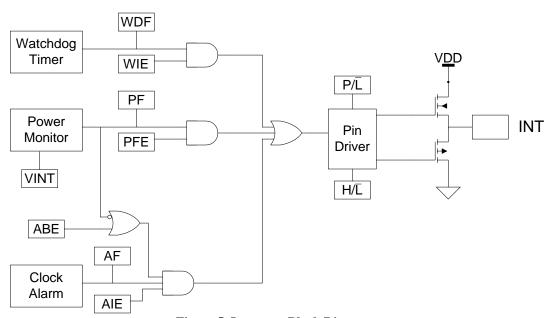


Figure 5. Interrupt Block Diagram

According to the programming selections, the pin can be driven in the backup mode for an alarm interrupt or not. In addition, the pin can be active low (opendrain) or active high (push-pull) driver. If programmed for operation during backup mode, it can only be active low. Lastly, the pin can provide a one-shot function so that the active condition is a pulse, or a level operation. In one-shot mode, the pulse width is fixed at approximately 200 ms. This mode is intended to reset a host microcontroller. In level mode, the pin goes to its active polarity until the

Flag register is read by the user. This mode is intended to be used as an interrupt to a host microcontroller. The control bits are summarized as follows.

<u>Watchdog Interrupt Enable</u> - WIE. When set to 1, the watchdog timer drives the interrupt pin as well as an internal flag when a watchdog timeout occurs. When set to 0, the watchdog timer affects only the internal flag.

Rev 0.2

Sept 2001 Page 13 of 27



<u>Alarm Interrupt Enable</u> – AIE. When set to 1, the alarm match drives the interrupt pin as well as an internal flag. When set to 0, the alarm match only affects the internal flag.

<u>Power-fail Interrupt Enable</u> - PFE. When set to 1, the power-fail monitor drives the pin as well as an internal flag. When set to 0, the power-fail monitor affects only the internal flag.

Alarm Battery-backup Enable - ABE. When set to 1, the clock alarm interrupt (as controlled by AIE) will function even in battery backup mode. When set to 0, the alarm will occur only when $V_{DD} > V_{LO}$. AIE should only be set when the interrupt pin is programmed for active low operation. In addition, it only functions with the clock alarm, not the watchdog. If enabled, the power monitor will drive the interrupt during all normal V_{DD} conditions regardless of the ABE bit. The application for ABE is intended for power control, where a system powers up at a predetermined time. Depending on the application, it may require dedicating the INT pin to this function.

 $\underline{\text{High/Low}}$ – H/L. When set to a 1, the INT pin is active high (push-pull). The INT pin can drive high only when $V_{DD}>V_{LO}$. When set to a 0, the interrupt

pin is active low (open-drain). It can function as a pull down even in battery backup mode.

<u>Pulse/Level</u> – P/L. When set to a 1, the INT pin is driven (by an interrupt source) for approximately 200 ms. When P/L is set to a 0, the interrupt pin is driven high or low (as set by H/L) until the flag register is read.

When an enabled interrupt source activates the INT pin, an external host can read the flag register to determine the cause. One or more flags may be set when the register is read, however all will be cleared when the register is read. If the INT pin is programmed for level mode, then the condition will clear and the INT pin will return to its inactive state. If the pin is programmed for pulsed operation, then reading the flag also will clear the flag and the pin. The pulse will not complete its specified duration if the flag register is read. Of course, if the INT pin is used to reset the host, then the flag register would not be read during an active pulse. Care should be taken in reading the flags as a new source may occur after the pin goes active but before the register is read.

During a power-on reset with no battery, the interrupt register is automatically loaded with the value 24h. This causes power fail interrupt to be enabled with an active low pulse.



FRAM Memory Operation

The memory array is logically organized as 32,768 x 8 with the upper 16 bytes disabled and allocated to the RTC. It is accessed using an industry standard SRAM-type parallel interface. It is virtually identical to the 32Kx8 FM1808 in function. The memory array in the FM3808 is inherently nonvolatile via its unique ferroelectric process. All data written to the part is immediately nonvolatile with no delay. Functional operation of the FRAM memory is similar to SRAM type devices. The major operating difference between the FRAM array and an SRAM (besides nonvolatile storage) is that the FM3808 latches the address on the falling edge of /CE.

Users access 32,752 memory locations each with 8 data bits through a parallel interface. The complete 15-bit address specifies each of 32,768 bytes uniquely, with the upper 16 locations allocated to timekeeping functions. Internally, the memory array is organized into 32 blocks of 8Kb each. The 5 most-significant address lines decode one of 32 blocks. This block segmentation has no effect on operation, however the user may wish to group data into blocks by its endurance requirements as explained in a later section.

The access and cycle time are the same for read and write memory operations. Writes occur immediately at the end of the access with no delay. A precharge operation, where /CE goes inactive, is a part of every memory cycle. Thus unlike SRAM, the access and cycle times are not equal.

The FM3808 is designed to operate in a manner very similar to other bytewide memory products. For users familiar with BBSRAM, the performance is comparable but the bytewide interface operates in a slightly different manner as described below. For users familiar with EEPROM, the obvious differences result from the higher write-performance of FRAM technology including NoDelay writes and much higher write-endurance.

Read Operation

A read operation begins on the falling edge of /CE. At this time, the address bits are latched and a memory cycle is initiated. Once started, a full memory cycle will be completed internally even if the /CE is taken inactive. Data becomes available on the bus after the access time has been satisfied.

After the address has been latched, the address value may be changed upon satisfying the hold time parameter. Unlike an SRAM, changing address values will have no effect on the memory operation after the address is latched.

The FM3808 will drive the data bus when /OE is asserted low. If /OE is asserted after the memory access time has been satisfied, the data bus will be driven with valid data. If /OE is asserted prior to completion of the memory access, the data bus will not be driven until valid data is available. This feature minimizes supply current in the system by eliminating transients due to invalid data. When /OE is inactive, the data bus will remain tri-stated.

Write Operation

Writes occur in the FM3808 in the same time interval as reads. The FM3808 supports both /CE and /WE controlled write cycles. In all cases, the address is latched on the falling edge of /CE.

In a /CE controlled write, the /WE signal is asserted prior to beginning the memory cycle. That is, /WE is low when /CE falls. In this case, the part begins the memory cycle as a write. The FM3808 will not drive the data bus regardless of the state of /OE.

In a /WE controlled write, the memory cycle begins on the falling edge of /CE. The /WE signal falls after the falling edge of /CE. Therefore, the memory cycle begins as a read. The data bus will be driven according to the state of /OE until /WE falls. The timing of both /CE and /WE controlled write cycles is shown in the electrical specifications.

Write access to the array begins asynchronously after the memory cycle is initiated. The write access terminates on the rising edge of /WE or /CE, whichever is first. Data set-up time, as shown in the electrical specifications, indicates the interval during which data cannot change prior to the end of the write access.

Unlike other truly nonvolatile memory technologies, there is no write delay with FRAM. Since the read and write access times of the underlying memory are the same, the user experiences no delay through the bus. The entire memory operation occurs in a single bus cycle. Therefore, any operation including read or write can occur immediately following a write. Data polling, a technique used with EEPROMs to determine if a write is complete, is unnecessary.

Precharge Operation

The precharge operation is an internal condition where the state of the memory is prepared for a new access. All memory cycles consist of a memory access and a precharge. The precharge is user initiated by taking the /CE signal high or inactive. It must remain high for at least the minimum precharge timing specification. The user dictates the beginning

Rev 0.2 Sept 2001 Page 15 of 27



of this operation since a precharge will not begin until /CE rises. However, the device has a maximum /CE low time specification that must be satisfied.

Memory Architecture

FRAM memory internally operates with a read and restore mechanism similar to a DRAM. Therefore each cycle (read or write) involves a change of state. The memory architecture is based on an array of rows and columns. Each access causes an endurance cycle for an entire row (4 bytes). The memory array is divided into 32 blocks, each 1Kx8. The 5-upper address lines decode the block selection as shown in Figure 6. Data targeted for significantly different numbers of cycles should be located in separate blocks since memory rows do not extend across block boundaries.

Each block of 1Kx8 consists of 256 rows and 4 column address locations. The address lines A0-A7 decode row selection and A8-A9 lines decode column selection. This scheme facilitates a relatively uniform distribution of cycles across the rows of a block. By allowing the address LSBs to decode row selection, the user avoids applying multiple cycles to the same row when accessing sequential data. For example, 256 bytes can be accessed sequentially without accessing the same row twice. In this example, one cycle would be applied to each row. An entire block of 1Kx8 can be read or written with only four cycles applied to each row. Figure 7 illustrates the organization within a memory block.

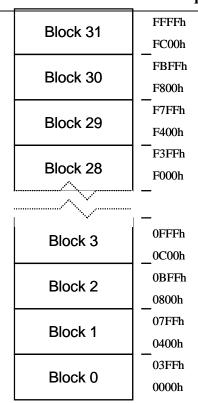


Figure 6. Address Blocks

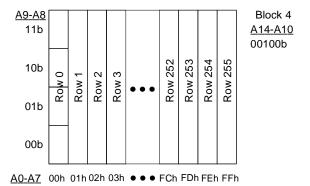


Figure 7. Row and Column Organization



FRAM Design Considerations

When designing with FRAM for the first time, users of SRAM will recognize a few minor differences. First, bytewide FRAM memories latch each address on the falling edge of chip enable. This allows the address bus to change after starting the memory access. Since every access latches the memory address on the falling edge of /CE, users should not ground it as they might with SRAM.

Users that are modifying existing designs to use FRAM should examine the hardware address decoders. Decoders should be modified to qualify addresses with an address valid signal if they do not already. In many cases, this is the only change required. Systems that drive chip enable active, then inactive for each valid address may need no modifications. An example of the target signal relationships are shown in Figure 8. Also shown is a common SRAM signal relationship that will not work for the FM3808.

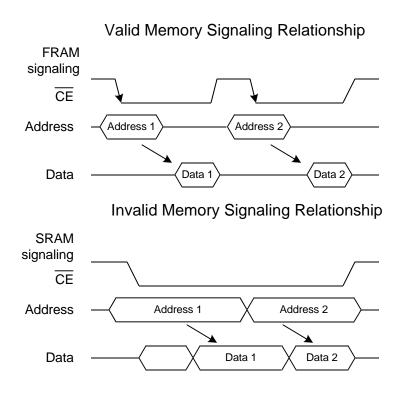


Figure 8. Memory Address Relationships



Real-time Clock Design Considerations

The principal design issues in using the real time clock are selection and specification of backup energy source and the selection of the timekeeping crystal. Selection of the backup source is primarily a choice between a capacitor and a battery, and the specifications needed for each. Selection of the crystal is based on mechanical (surface mount versus through-hole) considerations and the characteristic capacitance. Each topic is discussed briefly.

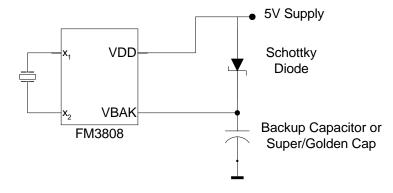
Backup Power Source

The FM3808 is designed to accommodate either a battery or a capacitor as a backup power source. Unlike SRAM-based timekeepers that depend on the battery to make data nonvolatile, the FM3808 is unrestricted. Data stored in FRAM is not dependent on the backup battery in any way. This means that capacitor backup, which should be less expensive, is a option. Selection of a capacitor is determined by the expected duration of power outage where timekeeping must be maintained, and the practical difficulty in resetting the time should it be lost. If the time is relatively easy to reset, or a typical power loss is only a brownout, the capacitor may be a good, cost effective choice. In addition, portable systems that use a battery for primary power are good candidates for capacitor backup. If the time is very difficult to reset, or the power outage may be longer than a capacitor can supply, then a small battery is best. Each system and application can be evaluated for the difficulty in setting the time. However, the expected backup times for several capacitor choices are illustrated below. These figures cannot be used as guarantees due to the unknown leakage characteristics in external components, but they provide guidelines for realistic expectations about capacitor use. In the scenario using capacitor backup, the charging circuit must also be considered. A typical representation is shown below.

The backup times are based on a starting backup voltage (fully charged) of 4.7V and minimum backup voltage of 2.5V. A 0.3V forward drop from 5.0V VDD might be expected from a schottky-diode. Note the graph, which shows approximate backup current as a function of backup voltage. Thus, the higher voltages at the beginning of discharge provide less incremental backup time than the lower voltages near the end of discharge. However, the total backup time depends on the capacitor size and the maximum, fully charged voltage.

One important note about capacitor backup is that the times are incremental. Each time power is restored the capacitor is fully recharged. Rather than examining the cumulative time without power in the system over a 10-year period, the capacitor design is only concerned with the maximum time without power for one outage.

If the times available for a capacitor are not sufficient, then a battery is the best selection. Most users opt for a 3V lithium coin. Note that with non-rechargeable batteries, the reservoir is not replenished so the critical parameter is the total time without power during the useful life of a system. For 1 year without power (total) during a 10-year system life, the battery capacity must be at least 9.25 mAhr. For 5 years without power during a 10-year period, it becomes 46 mA*hr.



Capacitor Size	Backup Time
100 μF	3 minutes
1000 μF	30 minutes
$10000 \mu F$	5.1 hours
0.47 F (super cap)	240 hours

Figure 9. Capacitor Backup Circuit

Rev 0.2 Sept 2001



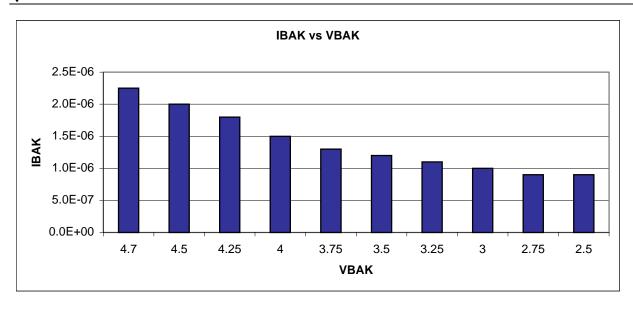


Figure 10. Backup Current vs. Voltage

Crystal Selection

The second passive component needed for the RTC function is the timekeeping crystal. A 32.768 kHz time-base is required, and the FM3808 is designed to accept a low cost crystal. The major parameters associated with the crystal are timekeeping accuracy and backup current. The FM3808 is designed to accept a crystal with a characteristic capacitance of 6 pF. Deviations from this specification will lead to different accuracy and IBAK from the specified values. Though accuracy is unlikely to improve, the

IBAK may go up or down from the specified value as a function of the capacitive load.

The timekeeping accuracy is also a strong function of the operating temperature due to errors in crystal frequency. Temperature behavior of timekeeping crystals is well known and it follows a curve like the one shown below. The specific crystal manufacturer should be consulted for the behavior of their specific device. Note the error in frequency ppm. One ppm is roughly 2.6 seconds per month in timekeeping error.

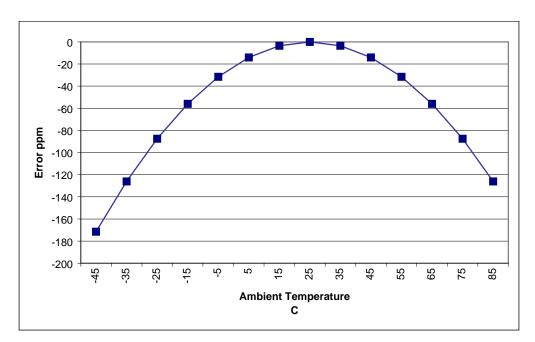


Figure 11. Typical Crystal Error vs. Temperature



Electrical Specifications

Absolute Maximum Ratings

Symbol	Description	Ratings
$V_{ m DD}$	Power Supply Voltage with respect to V _{SS}	-1.0V to +7.0V
V_{IN}	Voltage on any signal pin with respect to V _{SS}	-1.0V to +7.0V and
		$V_{IN} < V_{DD} + 1.0V$
T_{STG}	Storage temperature	-40°C to + 85°C
T_{LEAD}	Lead temperature (Soldering, 10 seconds)	300° C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only, and the functional operation of the device at these or any other conditions above those listed in the operational section of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

DC Operating Conditions ($T_A = -40^{\circ}$ C to $+85^{\circ}$ C, $V_{DD} = 4.5$ V to 5.5V unless otherwise specified)

Symbol	Parameter	Min	Тур	Max	Units	Notes
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V	
V _{INT}	V _{DD} Voltage that activates INT pin	4.6		4.75	V	2
		4.45		4.6	V	
V_{BAK}	Clock Backup Voltage	2.5	3.0	$V_{ m DD}$	V	
V_{LO}	V _{DD} Lockout Voltage	4.3		4.5	V	11
V_{SW}	V _{DD} Voltage that causes switch to V _{BAK}		V_{BAK}		V	4
V_{BG}	V _{DD} Voltage for active Power Monitor	2.3			V	5
I_{DD}	V _{DD} Supply Current - Active		10	25	mA	1
I_{SB1}	Standby Current - TTL			500	μΑ	6
I_{SB2}	Standby Current - CMOS			150	μΑ	7
I _{BAK}	Clock backup current		0.9	1.0	μΑ	3
I_{LI}	Input Leakage Current			10	μΑ	8
I_{LO}	Output Leakage Current			10	μΑ	8
V _{IH}	Input High Voltage	2.0		$V_{\rm DD} + 0.5$	V	
V_{IL}	Input Low Voltage	-0.5		0.8	V	
V _{OH}	Output High Voltage	2.4			V	10
V _{OL}	Output Low Voltage	•		0.4	V	9
V _{OLB}	Output Low Voltage (INT pin)			0.7	V	12
	Device in backup mode (V _{DD} <v<sub>BAK)</v<sub>					

Notes

- 1. V_{DD} = 5.5V, /CE cycling at minimum cycle time. All inputs at CMOS levels, all outputs unloaded.
- 2. Voltage for V_{INT} depends on selection of V_{INT} control bit.
- 3. $V_{BAK} = 3.0V$, $V_{DD} < V_{BAK}$; oscillator running.
- V_{SW} occurs when V_{DD} drops below V_{BAK}. V_{SW} is also the point at which the timekeeper draws current from the V_{BAK} pin, rather than from V_{DD}. V_{SW} is not otherwise used for control signals or functions.
- 5. Signals controlled by the power monitor (such as the INT output) are active.
- 6. $V_{DD} = 5.5V$, /CE at V_{IH} , All inputs at TTL levels, all outputs unloaded.
- 7. $V_{DD} = 5.5V$, /CE at V_{IH} , All inputs at CMOS levels, all outputs unloaded.
- 8. V_{IN} , V_{OUT} between V_{DD} and V_{SS} .
- 9. $I_{OL} = 4.2 \text{ mA}.$
- 10. $I_{OH} = -2.0 \text{ mA}.$
- 11. Memory and register access is blocked when $V_{DD} < V_{LO}$
- 12. $V_{DD}=0$, $V_{BAK}=3.0V$, $I_{OL}=4.2$ mA



Read Cycle AC Parameters ($T_A = -40^{\circ} \text{ C}$ to $+85^{\circ} \text{ C}$, $V_{DD} = 4.5 \text{ V}$ to 5.5 V unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Notes
t_{CE}	Chip Enable Access Time (to data valid)		70	ns	
t_{CA}	Chip Enable Active Time	70	10,000	ns	
t_{RC}	Read Cycle Time	130		ns	
t_{PC}	Precharge Time	60		ns	
t_{AS}	Address Setup Time	0		ns	
t_{AH}	Address Hold Time	10		ns	
t_{OE}	Output Enable Access Time		10	ns	
$t_{\rm HZ}$	Chip Enable to Output High-Z		15	ns	1
t_{OHZ}	Output Enable to Output High-Z		15	ns	1

Write Cycle AC Parameters ($T_A = -40^{\circ} \text{ C}$ to $+85^{\circ} \text{ C}$, $V_{DD} = 4.5 \text{ V}$ to 5.5 V unless otherwise specified)

Symbol	Parameter	Min	Max	Units	Notes
t_{CA}	Chip Enable Active Time	70	10,000	ns	
t_{CW}	Chip Enable to Write High	70		ns	
t _{WC}	Write Cycle Time	130		ns	
t _{PC}	Precharge Time	60		ns	
t _{AS}	Address Setup Time	0		ns	
t _{AH}	Address Hold Time	10		ns	
t_{WP}	Write Enable Pulse Width	30		ns	
t _{DS}	Data Setup	30		ns	
t_{DH}	Data Hold	0		ns	
t _{WZ}	Write Enable Low to Output High Z		15	ns	1
t _{WX}	Write Enable High to Output Driven	10		ns	1
$t_{\rm HZ}$	Chip Enable to Output High-Z		15	ns	1
t _{WS}	Write Setup	0		ns	2
t_{WH}	Write Hold	0		ns	2

Notes

- 1 This parameter is periodically sampled and not 100% tested.
- 2 The relationship between /CE and /WE determines if a /CE- or /WE-controlled write occurs. There is no timing specification associated with this relationship.

Power Cycle Timing $(T_A = -40^{\circ} \text{ C to} + 85^{\circ} \text{ C})$

Symbol	Parameter	Min	Max	Units	Notes
t _{INT}	INT signal active after V _{INT}		100	ns	1,2
t _{PD}	Last Access Complete to V _{LO}	0		ns	1,3
t_{RI}	VLO to inputs recognized on power-up	1		μs	1,4
t_R	Rise time of V_{DD} from V_{BG} to V_{LO}	100		μs	1,5
$t_{\rm F}$	Fall time of V_{DD} from V_{LO} to V_{BG}	100		μs	1,5

Notes

- 1 This parameter is periodically sampled and not 100% tested.
- 2 If power monitor is programmed to generate INT.
- 3 Access is blocked at V_{LO}. The last access should be complete prior to reaching V_{LO}. The early warning power fail interrupt may be useful in accomplishing this.
- 4 Failing to satisfy t_{RI} may result in the first access being ignored. Failure to raise /CE to a high level prior to V_{DD}>V_{LO} may result in improper operation.
- 5 Slew rate for proper transition between the locked-out condition and normal operation.



Supervisor AC Parameters ($T_A = -40^{\circ}$ C to $+85^{\circ}$ C, $V_{DD} = 4.5$ V to 5.5V unless otherwise specified)

Symbol	Parameter	Min	Тур	Max	Units	Notes
t_{IPU}	INT output pulse width	150	200	300	ms	1
t_{FCO}	Flag register access to INT pin clear	-		100	ns	2

Notes

- 1 P/L = 1; pulse mode.
- 2 P/L= 0; level mode. From the end of the access where the flag register is read and the flag cleared.

Data Retention ($V_{DD} = 4.5V$ to 5.5V unless otherwise specified)

Parameter	Min	Units	Notes
Data Retention	10	Years	1

Notes

1. The relationship between retention, temperature, and the associated reliability level will be characterized separately.

Capacitance $(T_A = 25^{\circ} \text{ C, f} = 1.0 \text{ MHz, V}_{DD} = 5 \text{ V})$

Symbol	Parameter	Max	Units	Notes
C_{IO}	Input/output capacitance (DQ)	8	pF	1
C_{I}	Input capacitance	6	pF	1
C_{XTAL}	X1, X2 Crystal pin capacitance	12	pF	1, 2

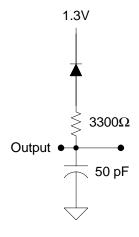
Notes

- 1 This parameter is periodically sampled and not 100% tested.
- 2 The crystal attached to the X1/X2 pins must be rated as 6pF max.

AC Test Conditions

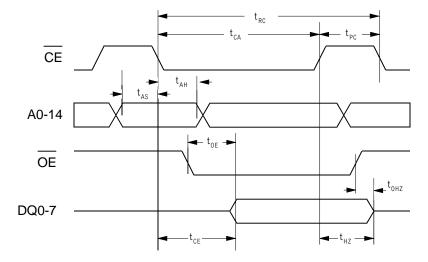
Input Pulse Levels 0 to 3V Input rise and fall times 10 ns Input and output timing levels 1.5V

Equivalent AC Load Circuit

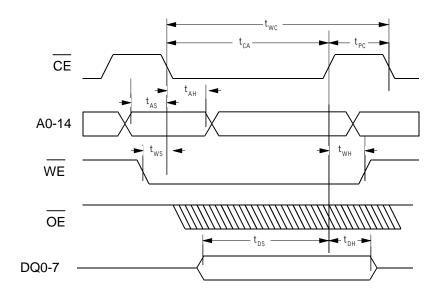




Timing Diagrams

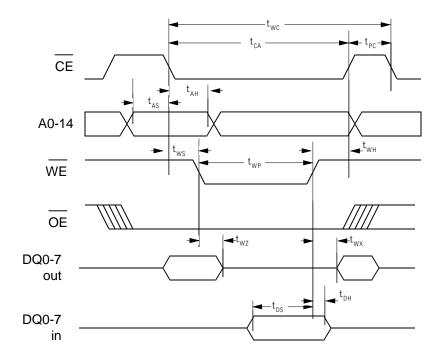


Read Cycle Timing



Write Cycle Timing - /CE Controlled Timing

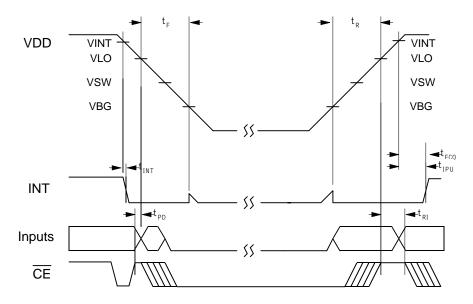




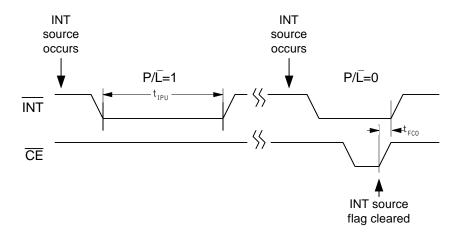
Write Cycle Timing - /WE Controlled Timing



Picture assumes VSW < VINT



Power Cycle Timing



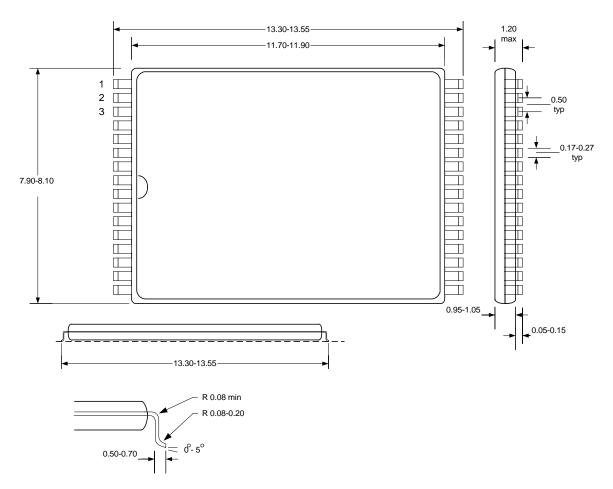
INT Pin Timing



Mechanical Drawing

32-pin TSOP (JEDEC MO-142 BA)

All dimensions in millimeters





Revision History

Revision	Date	Summary of Changes
0.1	Dec 19, 2000	Initial Release
0.2	Sept 19, 2001	Changed I _{SB} spec, redefined crystal capacitance specs, data retention
		temperature condition. General cleanup.